

UHB100SC12E1BC3N

1200V 100A SiC, Half-Bridge, G3, E1BN

Package Type: E1B
 Process Technology: SiC, Si
 Date Issued: 01/15/2024
 Document Number: QDN1SGLB -PQ030 rev A

TEST NAME	TEST STANDARD AND CONDITIONS	# SAMPLES x # LOTS	TEST RESULTS
High Temperature Gate Bias (HTGB)	JESD22-A108: T _J =150°C, V _{GS} =+20V, 2000 hrs	6 pcs x 3 lots	6 pcs x 3 lots Pass 0 pcs Fail
High Temperature Reverse Bias (HTRB)	MIL-STD-750-1 M1038 Method A: T _J =150°C, V _{DS} = 80% V _{DS,MAX} =960V 2000 hrs	6 pcs x 3 lots	6 pcs x 3 lots Pass 0 pcs Fail
Highly Accelerated Stress Test (HAST)	IEC 60068-2-67: 135°C, RH = 85%, 96 hrs, V _{ds} =42V, V _{gs} = 0V	6 pcs x 3 lots	6 pcs x 3 lots Pass 0 pcs Fail
Temperature Cycling (TC) †	JESD22-A104: 300 cycles, -40°C to +125°C, 2 cycles/hour,	6 pcs x 3 lots	6 pcs x 3 lots Pass 0 pcs Fail
Intermittent Operating Life (IOL) †	MIL-STD-750 Method 1037: ΔT _J ≥100°C, 20,000 cycles (Ton/Toff dependent on device)	6 pcs x 3 lots	6 pcs x 3 lots Pass 0 pcs Fail
Conclusion	This part meets Qorvo's product qualification requirements.		

Qualification Samples:

- QBG1CGLB – UFB15C12E1BC3N – 1 Lot
- QDN1SGLB – UHB100SC12E1BC3N – 1 Lot
- USP50SC12E1BC3N – 1 Lot

Products Qualified by Similarity:

- QBK1SGLB – UFB25SC12E1BC3N
- QDL1SGLB – UHB50SC12E1BC3N